

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

*In re* U.S. Patent No. 7,002,302

Docket No.: 61610074US

Park, *et al.*

Application No.: 10/673,152

Group Art Unit: 2828

Confirmation No.: 9796

Filed: September 30, 2003

Examiner: VU, David Hung

For: **FLAT PANEL DISPLAY**

**Mail Stop Post Issue**

Attn: Certificate of Correction Branch  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**REQUEST FOR CERTIFICATE OF CORRECTION  
UNDER 37 C.F.R. 1.323  
APPLICANTS' MISTAKE**

Sir:

Transmitted herewith in duplicate is PTO Form PTO/SB/44 - Certificate of Correction for the above-identified U.S. Patent correcting the Applicants' mistakes as shown in the enclosed Certificate of Correction form.

Since these mistakes are clerical, typographical, and/or minor, and the proposed correction does not involve changes that would constitute new matter or require reexamination, Applicants respectfully submit that issuance of a Certificate of Correction is in order. Since these errors were due to the Applicants' mistake, Applicants submit a fee in the amount of \$100.00. Any deficiencies are hereby authorized to be charged to our Deposit Account No. 50-3698.

## REMARKS

Applicants respectfully submit that the mistakes to be corrected are clerical, typographical, and/or minor, and the proposed correction does not involve changes that would constitute new matter or require reexamination. These changes render the corrected portions of the specification and drawings consistent with the applicable uncorrected portions of the specification and drawings.

### **Proposed corrections to the specification:**

The paragraph beginning on page 1, line 4 will be amended as follows:

This application claims the benefit of Korean Patent Application No. 2002-61082 filed on ~~Oct. 7, 2003~~ Oct. 7, 2002 and Korean Patent Application No. 2003-24508 filed on Apr. 17, 2003, the disclosures of which are hereby incorporated herein by reference in their entirety.

The paragraph beginning on page 3, line 10 will be amended as follows:

Namely, referring to FIG. 9 illustrating a relation of drain current ( $I_d$ ) to gate voltage ( $V_g$ ) of the driving transistor, the amount of current of 1  $\mu A$  or more that is about 4-~~order~~ 1-order larger than 90 nA, an on current value suitable for light emitting diodes of 180 ppi or more, flows through the driving transistor 155 in a conventional organic light emitting diode. Therefore, there are problems in that on current of the driving transistor should be reduced to obtain luminance suitable for an AMOLED of 180 ppi or more.

The paragraph beginning on page 10, line 8 will be amended as follows:

Referring to FIG. 4A and FIG. 4B, the driving transistor according to the second preferred embodiment is formed by changing shape of a semiconductor layer 420 and has the almost similar structure to the driving transistor according to the first preferred embodiment illustrated in FIG. 3A and FIG. 3B except that an offset region 430 between multiple gates 441 and 445 ~~are formed~~ is formed in a zigzag shape differently from the first preferred embodiment so that a resistance value of the driving transistor is increased. The zigzag shaped offset region 430 is a high resistance region of a low concentration impurity region on which the same conductivity impurities as high concentration source/drain regions 461 ~~and 465~~ 421 and 425 are doped at a low concentration or an intrinsic region on which impurities are not doped. Furthermore, the zigzag shaped offset region 430 can be formed into a high resistance region on which low concentration impurities having the same conductivity type as the high concentration source/drain regions 461 ~~and 465~~ 421 and 425 are partially doped.

The paragraph beginning on page 11, line 15 will be amended as follows:

That is, the offset region 530 of the driving transistor according to the third preferred embodiment is consisted of portions 535 on which the same conductivity type low concentration impurities as high concentration source/drain regions 561 ~~and 565~~ 521 and 525 are doped and a portion 531 between the portions 535 on which impurities are not doped.

The paragraph beginning on page 12, line 15 will be amended as follows:

That is, in the offset region 630 of the driving transistor according to the fourth preferred embodiment, a resistance value of the driving transistor is ~~reduced~~ increased by narrowing width compared with the first preferred embodiment as maintaining length (Ld) equally to that in the first preferred embodiment, thereby changing size (Wd/Ld) of the offset region 630, wherein the offset region 630 is a high resistance region on which low concentration impurities having the same conductivity type as high concentration source/drain regions ~~661 and 665~~ 621 and 625 are doped or not doped.

The paragraph beginning on page 14, line 14 will be amended as follows:

In an organic light emitting diode according to the fifth preferred embodiment, the driving transistor reduces the amount of current flowing to the EL device as maintaining high speed switching operation of the switching transistor as it is by changing resistance value of the driving transistor according to size and doping concentration of the high resistance offset ~~region 730~~ regions 723 and 727 of the driving transistor.

**Proposed corrections to the drawings:**

Figure 2 will be amended by changing reference numeral "256" to "265." Support for these amendments may be found at least in the paragraph beginning on column 1, line 61.

Figure 7 will be amended by changing reference numeral "761" (under numeral "755") to "765." Support for these amendments may be found at least in the paragraph beginning on page 13, line 17.

Prompt and favorable consideration of this Request is respectfully requested.

Respectfully submitted,

/hae-chan park/

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Date: March 9, 2007

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## UNITED STATES PATENT AND TRADEMARK OFFICE

### CERTIFICATE OF CORRECTION

PATENT NO : 7,002,302

Page 1 of 1

DATED : February 21, 2006

INVENTOR(S) : Sang-Il PARK and Jae Bon KOO

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

Column 1, line 7, "Oct. 7, 2003" should be changed to -- Oct. 7, 2002 --.

Column 2, line 19, "1-oder" should be changed to -- 1-order --.

Column 6,

line 2, "are formed" should be changed to -- is formed --;

line 8, "461 and 465" should be changed to -- 421 and 425 --;

line 13, "461 and 465" should be changed to -- 421 and 425 --;

line 45, "561 and 565" should be changed to -- 521 and 525 --.

Column 7,

line 12, "reduced" should be changed to -- increased --;

line 19, "661 and 665" should be changed to -- 621 and 625 --.

Column 8, line 21, "region 730" should be changed to -- regions 723 and 727 --.

Figure 2, reference numeral "256" should be changed to -- 265 --.

Figure 7, reference numeral "761" (under numeral "755") should be changed to -- 765 --.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

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This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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